Silicon NPN Epitaxial

HITACHI

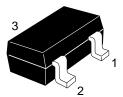
ADE-208-1144 (Z) 1st. Edition Mar. 2001

Application

Low frequency amplifier, Muting

Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	15	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I _c	0.7	А
Collector power dissipation	P _c	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

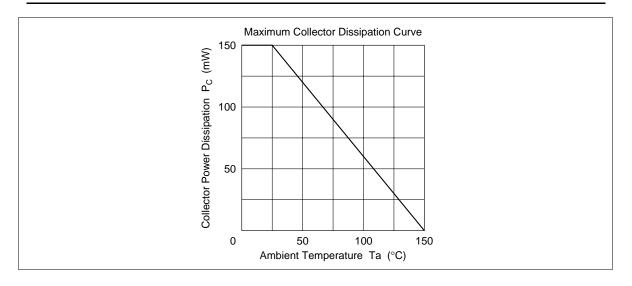
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	15	_	_	V	I_{C} = 1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	1.0	μΑ	$V_{CB} = 20 \text{ V}, I_{E} = 0$
DC current transfer ratio	h _{FE} *1	250	_	800		$V_{CE} = 1 \text{ V}, I_{C} = 150 \text{ mA}^{*2}$
Base to emitter voltage	V_{BE}	_	_	1.0	V	$V_{CE} = 1 \text{ V}, I_{C} = 150 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	0.5	V	$I_{\rm C}$ = 500 mA, $I_{\rm B}$ = 50 mA* ²
Gain bandwidth product	f⊤	_	250	_	MHz	$V_{CE} = 1 \text{ V}, I_{C} = 150 \text{ mA}^{*2}$

Notes: 1. The 2SD1306 is grouped by $h_{\rm FE}$ as follows.

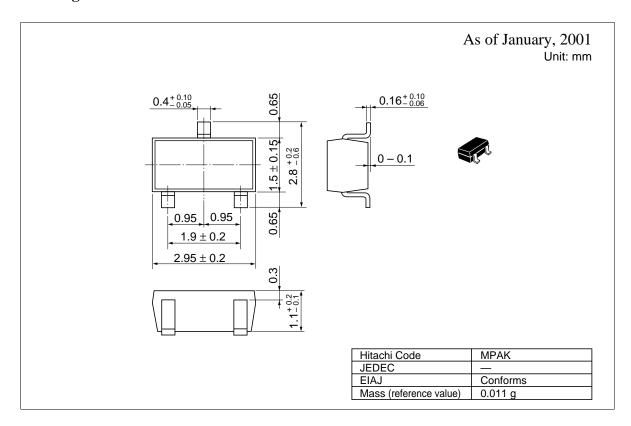
2. Pulse test

Grade	D	E
Mark	ND	NE
h _{FE}	250 to 500	400 to 800

See characteristic curves of 2SD1504.



Package Dimensions



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